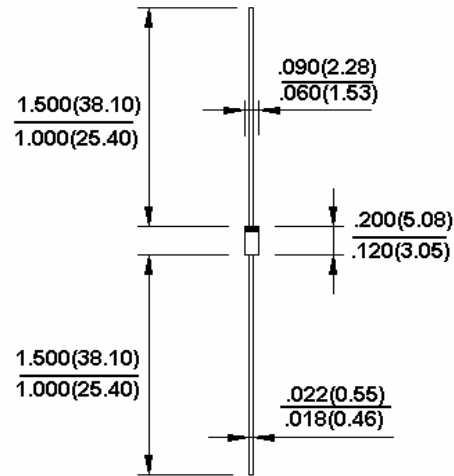


DO-35

Features

- ◇ Fast switching device ($T_{RR} < 4.0\text{nS}$)
- ◇ DO-35 package (JEDEC)
- ◇ Through-hole device type mounting
- ◇ Hermetically sealed glass
- ◇ Compression bonded construction
- ◇ All external surface are corrosion resistant and leads are readily solderable
- ◇ RoHS compliant
- ◇ Solder hot dip Tin(Sn) lead finish
- ◇ Cathode indicated by polarity band



Dimensions in inches and(millimeters)

Maximum Ratings and Electrical Characteristics

Rating at 25°C ambient temperature unless otherwise specified.

Maximum Ratings

Type Number	Symbol	Value	Units
Power Dissipation	P_d	500	mW
Working Inverse Voltage	W_{IV}	75	V
Non-repetitive Peak Forward Current	I_{FM}	450	mA
Average Rectified Current	I_o	150	mA
Peak Forward Surge Current	I_{FSURGE}	2	A
Operating Junction Temperature	T_J	175	°C
Storage Temperature Range	T_{STG}	-65 to + 200	°C

Electrical Characteristics

Type Number	Symbol	Min	Max	Units
Breakdown Voltage IR=100uA IR=5uA	B_V	100 75		V
Forward Voltage 1N4448, 1N914B IF=5.0mA 1N4148 IF= 10mA 1N4448, 1N914B IF =100mA	V_F	0.62	0.72 1.0 1.0	V
Reverse Leakage Current VR=20V VR=75V	I_R		25 5	nA uA
Junction Capacitance VR=0, f=1.0MHz	C_j	-	4.0	pF
Reverse Recovery Time (Note 1)	t_{rr}	-	4.0	nS

Notes: 1. Reverse Recovery Test Conditions: $I_F=10\text{mA}$, $V_R=6\text{V}$, $R_L=100\Omega$, $I_{RR}=1\text{mA}$

RATINGS AND CHARACTERISTIC CURVES (1N4448/1N4148/1N914B)

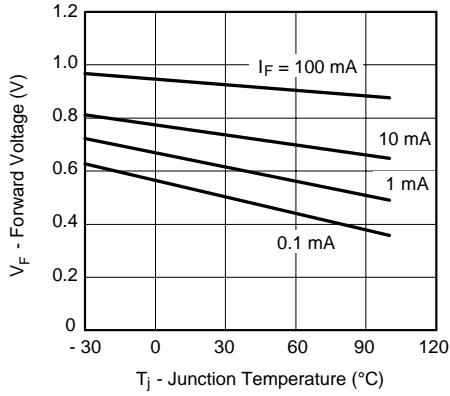


Figure 1. Forward Voltage vs. Junction Temperature

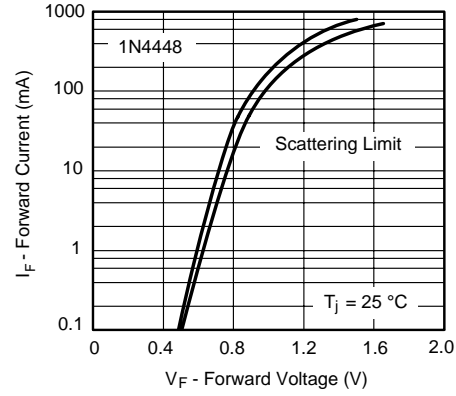


Figure 3. Forward Current vs. Forward Voltage

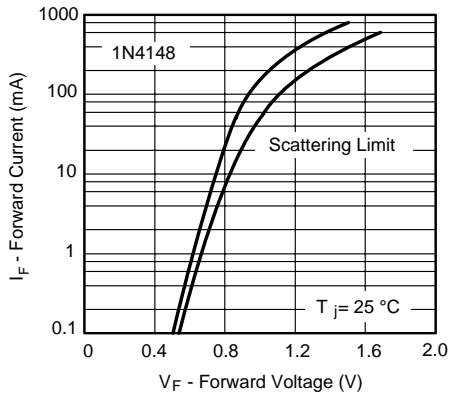


Figure 2. Forward Current vs. Forward Voltage

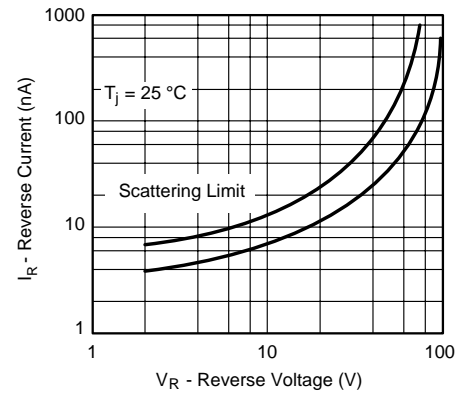


Figure 4. Reverse Current vs. Reverse Voltage

PACKAGE	SPQ/PCS	CARTON SPQ/PCS	CARTON SIZE/CM	CARTON GW/KG	CARTON NW/KG
DO-35	5000/AMMO	100000	41X28.5X38	14.57	13.07